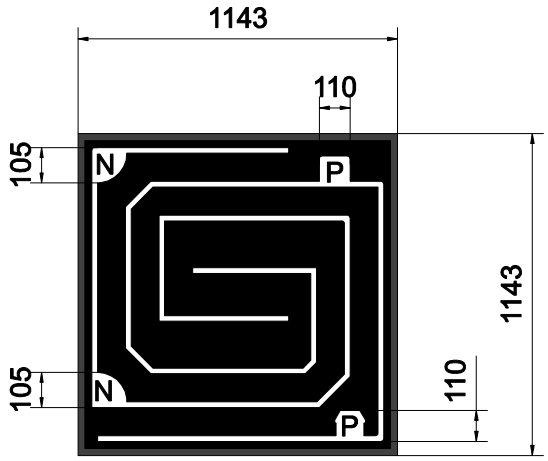
# LED - Chip

# ELC-460-31-2

26.05.2008 rev. 02

| Radiation | Type | Technology | Electrodes |
|---|---|---|---|
| Blue | | $InGaN/Al_2O_3$ | Both on top side |




typ. dimensions (µm)

typ. thickness
100 (±10) µm

p and n contact
gold alloy

backside metalization
gold alloy

## Optical and Electrical Characteristics

$T_{amb}$ = 25℃, unless otherwise specified

| Parameter | Test conditions | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Forward voltage | $I_F$ = 20 mA | $V_F$ | | 2.7 | 3.1 | V |
| Forward voltage[2] | $I_F$ = 350 mA | $V_F$ | | 3.5 | | V |
| Reverse voltage | $I_R$ = 10 µA | $V_R$ | 5V | | | V |
| Radiant power[1] | $I_F$ = 20 mA | $\Phi_e$ | 14 | 18 | | mW |
| Radiant power[1] | $I_F$ = 350 mA | $\Phi_e$ | 200 | 250 | | mW |
| Luminous intensity[1] | $I_F$ = 350 mA | $I_v$ | 1500 | 2500 | | mcd |
| Peak wavelength | $I_F$ = 350 mA | $\lambda_P$ | 445 | 455 | 465 | nm |
| Dominant wavelength | $I_F$ = 350 mA | $\lambda_D$ | 455 | 465 | 475 | nm |
| Spectral bandwidth at 50% | $I_F$ = 20 mA | $\Delta\lambda_{0.5}$ | | 25 | | nm |
| Switching time | $I_F$ = 20 mA | $t_r$, $t_f$ | | 50 | | ns |

[1]Measured on bare chip with *EPIGAP* equipment

## Labeling

| Type | Lot N° | $I_V$(typ) [mcd] | $V_F$(typ) [V] | Quantity |
|---|---|---|---|---|
| ELC-460-31-2 | | | | |

**Packing:** Chips on adhesive film with wire-bond side on top



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